

## 2N3702



Inis device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings\*

| Symbol                            | Parameter  | Value       | Units |
|-----------------------------------|--|-------------|-------|
| $V_{CEO}$                         | Collector-Emitter Voltage                        | 25          | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 40          | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 5.0         | V     |
| I <sub>C</sub>                    | Collector Current - Continuous                   | 500         | mA    |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range | -55 to +150 | °C    |

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

| Symbol          | Characteristic                          | Max    | Units |
|-----------------|---|--------|-------|
|                 |   | 2N3702 |       |
| P <sub>D</sub>  | Total Device Dissipation                | 625    | mW    |
|                 | Derate above 25°C                       | 5.0    | mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 83.3   | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200    | °C/W  |

# PNP General Purpose Amplifier (continued)

| Flactrical | Chara  | 4:-1:     |
|------------|--------|-----------|
| Flectrical | Charac | teristics |

| Symbol               | Parameter                                | Test Conditions                                 | Min | Max  | Units |
|----------------------|--|---|-----|------|-------|
|                      |  |   |     |      |       |
| OFF CHA              | RACTERISTICS                             |   |     |      |       |
| $V_{(BR)CEO}$        | Collector-Emitter Breakdown Voltage*     | $I_C = 100 \mu A, I_B = 0$                      | 25  |      | V     |
| V <sub>(BR)CBO</sub> | Collector-Base Breakdown Voltage         | $I_C = 10 \text{ mA}, I_E = 0$                  | 40  |      | V     |
| V <sub>(BR)EBO</sub> | Emitter-Base Breakdown Voltage           | $I_E = 100  \mu A,  I_C = 0$                    | 5.0 |      | V     |
| I <sub>CBO</sub>     | Collector Cutoff Current                 | $V_{CB} = 20 \text{ V}, I_{E} = 0$              |     | 100  | nA    |
| I <sub>EBO</sub>     | Emitter Cutoff Current                   | $V_{EB} = 3.0 \text{ V}, I_{C} = 0$             |     | 100  | nA    |
| ON CHAR              | RACTERISTICS*                            | $V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$ | 60  | 300  |       |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage     | $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$     |     | 0.25 | V     |
| V <sub>BE(on)</sub>  | Base-Emitter On Voltage                  | $V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$ | 0.6 | 1.0  | V     |
|                      |  | - 10  | /14 |      |       |
| SMALL S              | IGNAL CHARACTERISTICS                    | 4 1 3 3   | CIN |      |       |
| SMALL S              | IGNAL CHARACTERISTICS Output Capacitance | $V_{CB} = 10 \text{ V, f} = 1.0 \text{ MHz}$    | cn  | 12   | pF    |

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

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